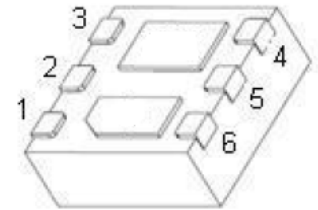


DFNWB2X2-6L Plastic-Encapsulate MOSFETS

CJMPD11 Dual P-Channel Power MOSFET

| $V_{(BR)DSS}$ | $R_{DS(on)MAX}$ | I_D |
|---------------|-----------------|--------|
| -20V | 110mΩ@-4.5 V | -2.3 A |
| | 140mΩ@-2.5 V | |

DFNWB2*2-6L



General Description

The CJMPD11 uses advanced trench technology and design to Provide excellent $R_{DS(on)}$ with low gate charge. This device is suitable for use in DC-DC conversion applications.

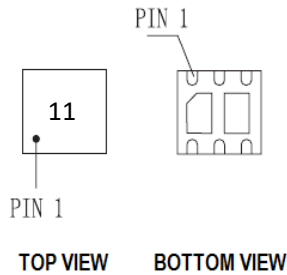
FEATURE

- Low Profile for Easy Fit in Thin Environments
- Bidirectional Current Flow with Common Source Configuration

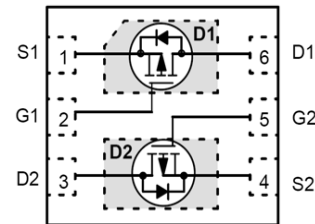
APPLICATIONS

- Optimized for Battery and Load Management Applications in Portable Equipment
- Li-Ion Battery Charging and Protection Circuits
- High Power Management in Portable , Battery Powered Products
- High Side Load Switch

MARKING:



Equivalent Circuit



Maximum ratings ($T_a=25^{\circ}C$ unless otherwise noted)

| Parameter | Symbol | Value | Unit |
|---|-----------------|-----------|---------------|
| Drain-Source Voltage | V_{DS} | -20 | V |
| Gate-Source Voltage | V_{GS} | ±8 | V |
| Continuous Drain Current | I_D | -2.3 | A |
| Pulsed Drain Current ($t=300\mu s$) | I_{DM} | -10 | A |
| Power Dissipation | P_D | 0.35 | W |
| Thermal Resistance from Junction to Ambient | $R_{\theta JA}$ | 357 | $^{\circ}C/W$ |
| Junction Temperature | T_J | 150 | $^{\circ}C$ |
| Storage Temperature | T_{STG} | -55~ +150 | $^{\circ}C$ |

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

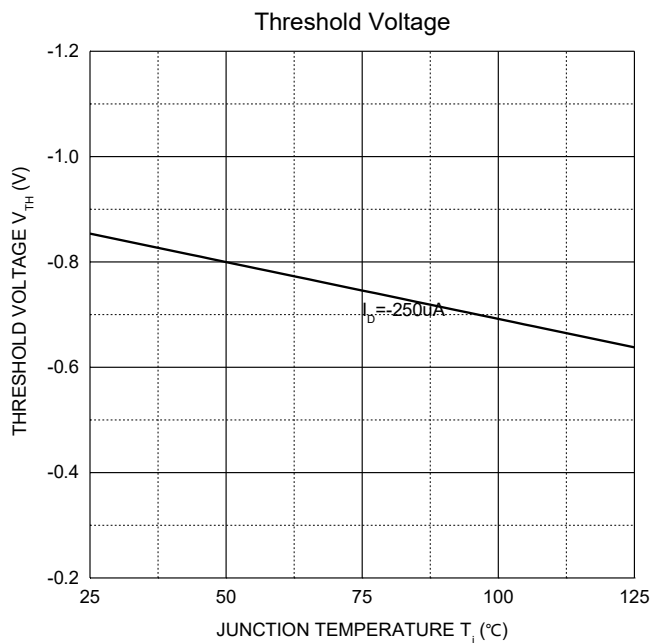
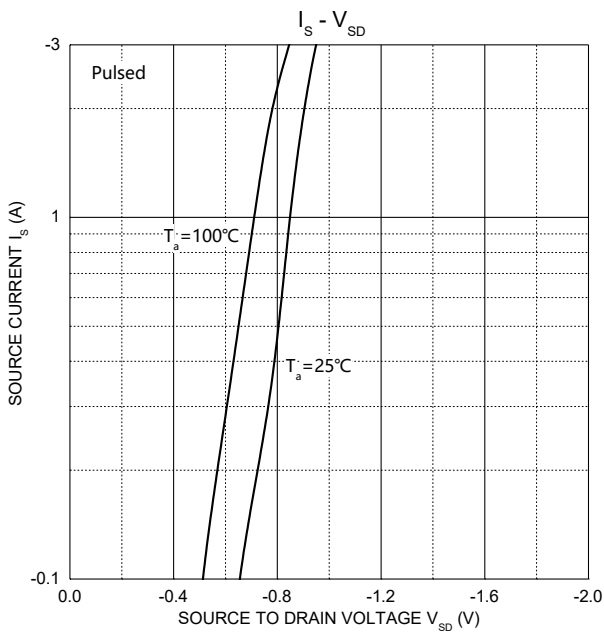
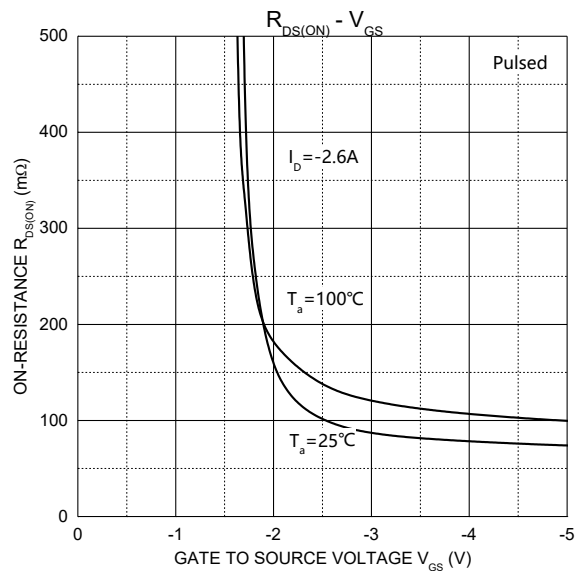
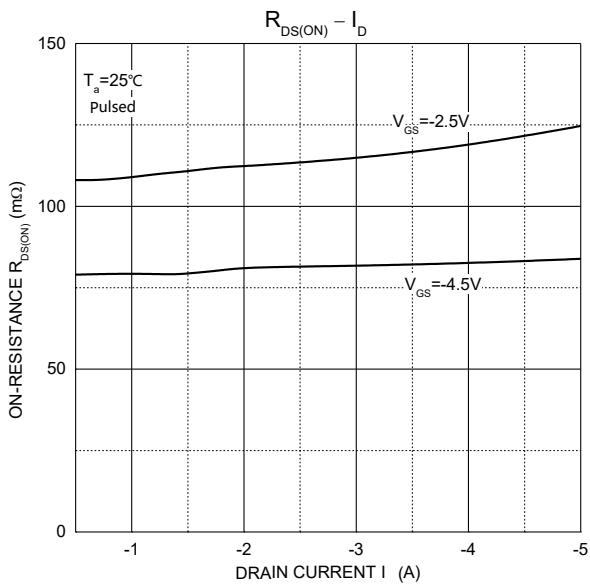
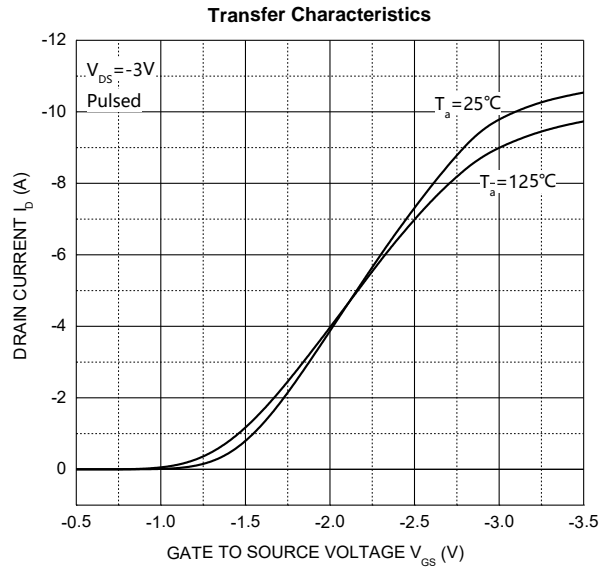
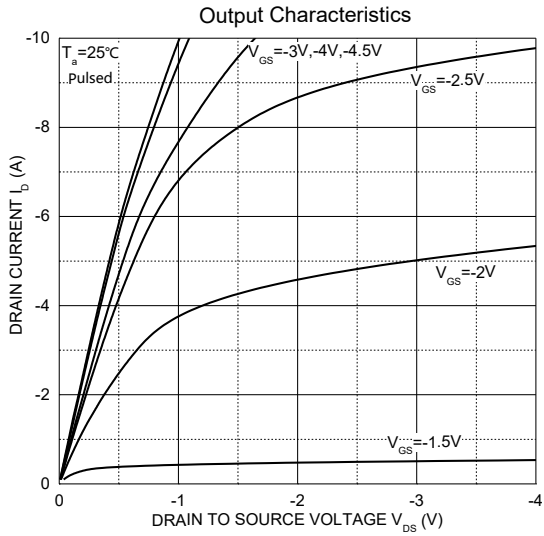
| Parameter | Symbol | Test Condition | Min | Type | Max | Unit |
|--|---------------|--|------|------|-----------|------------|
| Static Characteristics | | | | | | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS} = 0V, I_D = -250\mu A$ | -20 | | | V |
| Zero gate voltage drain current | I_{DSS} | $V_{DS} = -16V, V_{GS} = 0V$ | | | -1 | μA |
| Gate-body leakage current | I_{GSS} | $V_{GS} = \pm 8V, V_{DS} = 0V$ | | | ± 100 | nA |
| Gate threshold voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\mu A$ | -0.4 | -0.7 | -1 | V |
| Drain-source on-resistance ^a | $R_{DS(on)}$ | $V_{GS} = -4.5V, I_D = -3A$ | | 70 | 110 | m Ω |
| | | $V_{GS} = -2.5V, I_D = -2A$ | | 110 | 140 | |
| Forward tranconductance ^a | g_{FS} | $V_{DS} = -5V, I_D = -2A$ | 5 | | | S |
| Dynamic characteristics^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$ | | 405 | | pF |
| Output Capacitance | C_{oss} | | | 75 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 55 | | |
| Gate resistance | R_g | $f = 1MHz$ | | 6 | | Ω |
| Total Gate Charge | Q_g | $V_{DS} = -10V, V_{GS} = -2.5V, I_D = -3A$ | | 3.3 | 12 | nC |
| Gate-Source Charge | Q_{gs} | | | 0.7 | | |
| Gate-Drain Charge | Q_{gd} | | | 1.3 | | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = -10V, V_{GEN} = -4.5V, I_D = -1A$ $R_L = 10\Omega, R_{GEN} = 1\Omega$ | | 11 | | ns |
| Turn-on rise time | t_r | | | 35 | | |
| Turn-off delay time | $t_{d(off)}$ | | | 30 | | |
| Turn-off fall time | t_f | | | 10 | | |
| Source-Drain Diode characteristics | | | | | | |
| Diode forward current | I_S | $T_C = 25^\circ\text{C}$ | | | -2.3 | A |
| Diode pulsed forward current ^a | I_{SM} | | | | -10 | A |
| Diode Forward voltage | V_{DS} | $V_{GS} = 0V, I_S = -1.3A$ | | | -1.2 | V |

Notes :

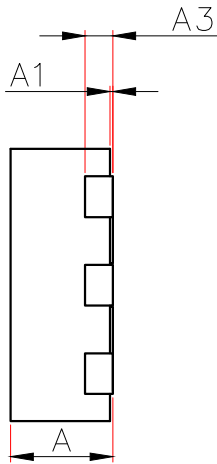
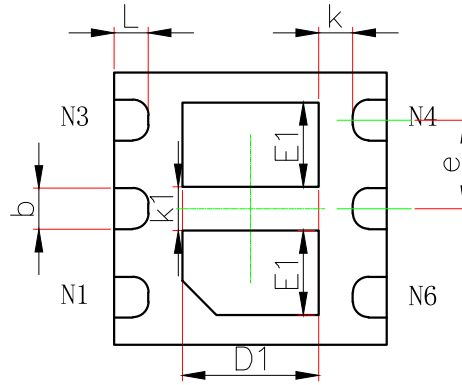
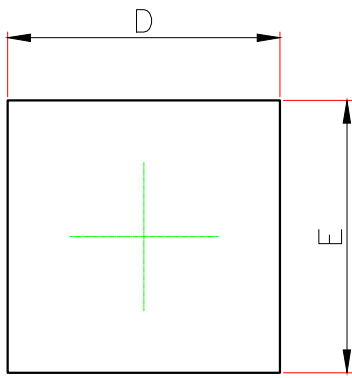
a. Pulse Test : Pulse Width < 300 μs , Duty Cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.

Typical Characteristics

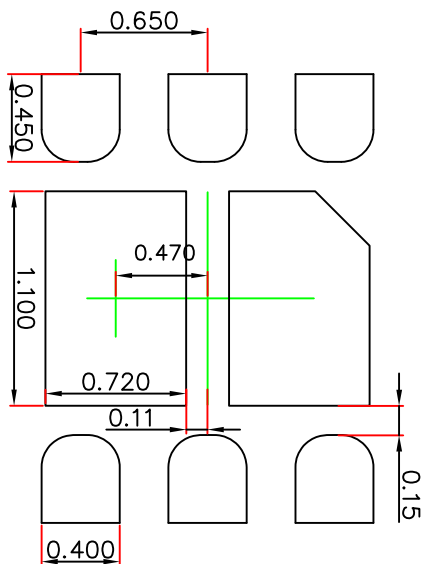


DFNWB2X2-6L Package Outline Dimensions



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 0.700 | 0.800 | 0.028 | 0.031 |
| A1 | 0.000 | 0.050 | 0.000 | 0.002 |
| A3 | 0.203REF. | | 0.008REF. | |
| D | 1.900 | 2.100 | 0.075 | 0.083 |
| E | 1.900 | 2.100 | 0.075 | 0.083 |
| D1 | 0.900 | 1.100 | 0.035 | 0.043 |
| E1 | 0.520 | 0.720 | 0.020 | 0.028 |
| b | 0.250 | 0.350 | 0.010 | 0.014 |
| e | 0.650TYP. | | 0.026TYP. | |
| k | 0.200MIN. | | 0.008MIN. | |
| k1 | 0.320REF. | | 0.013REF. | |
| L | 0.200 | 0.300 | 0.008 | 0.012 |

DFNWB2X2-6L Suggested Pad Layout



Note:

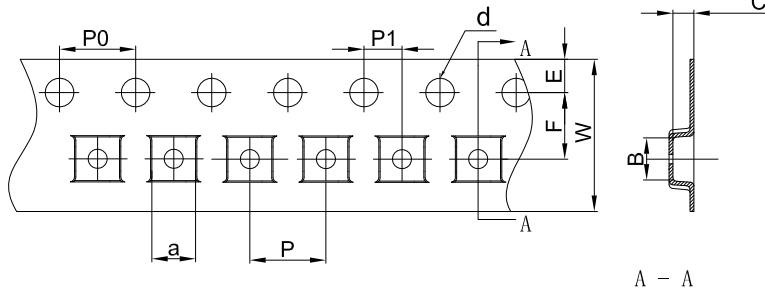
1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.050 mm.
3. The pad layout is for reference purposes only.

NOTICE

JSCJ reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

DFNWB2X2-6L Tape and Reel

DFNWB2×2-6L Embossed Carrier Tape



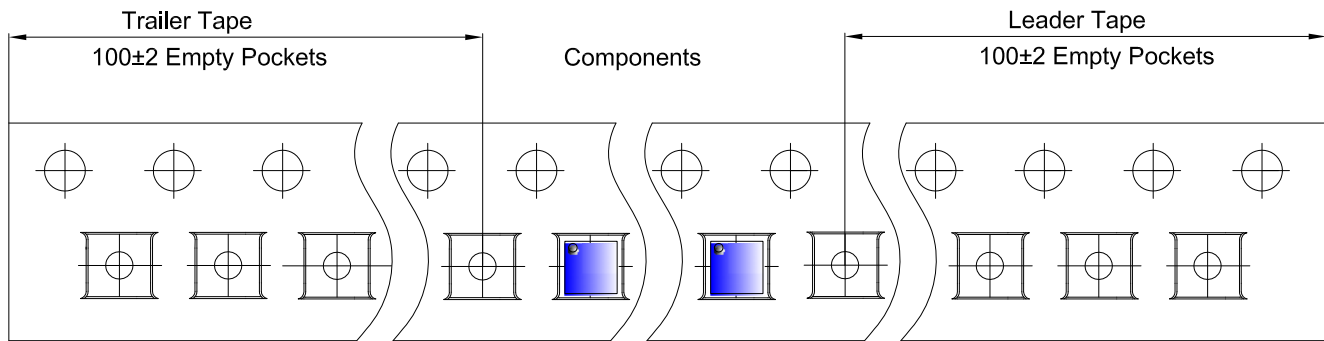
Packaging Description:

DFNWB2×2-6L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 18.0cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

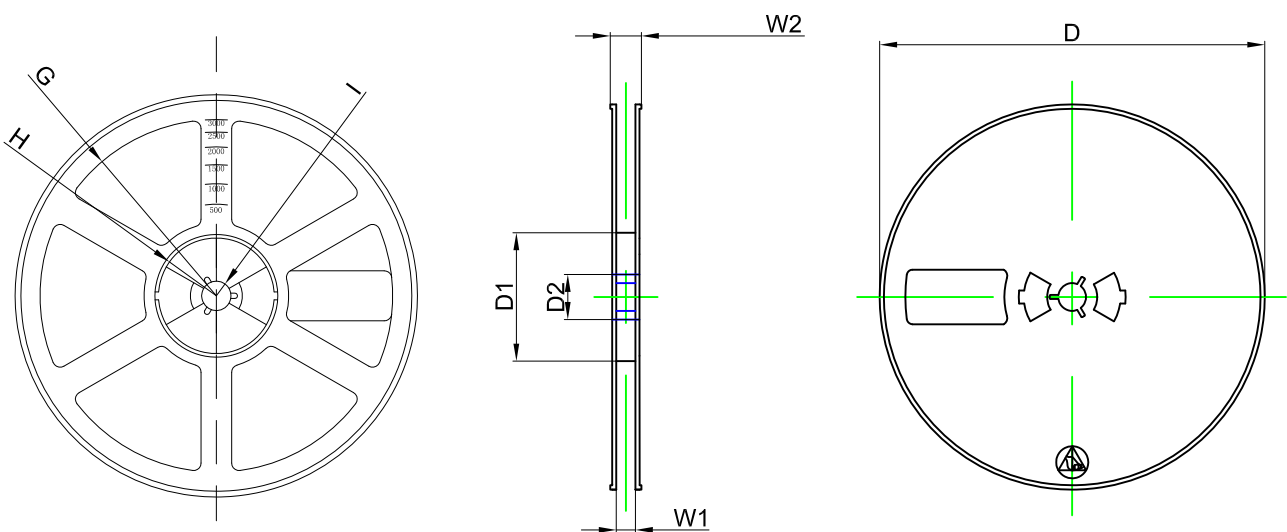
Dimensions are in millimeter

| Pkg type | a | B | C | d | E | F | P0 | P | P1 | W |
|-------------|------|------|------|-------|------|------|------|------|------|------|
| DFNWB2×2-6L | 2.30 | 2.30 | 1.10 | Ø1.50 | 1.75 | 3.50 | 4.00 | 4.00 | 2.00 | 8.00 |

DFNWB2×2-6L Tape Leader and Trailer



DFNWB2×2-6L Reel



Dimensions are in millimeter

| Reel Option | D | D1 | D2 | G | H | I | W1 | W2 |
|-------------|---------|-------|-------|--------|--------|-------|------|-------|
| 7" Dia | Ø180.00 | 60.00 | 13.00 | R78.00 | R25.60 | R6.50 | 9.50 | 13.10 |

| REEL | Reel Size | Box | Box Size(mm) | Carton | Carton Size(mm) | G.W.(kg) |
|----------|-----------|------------|--------------|-------------|-----------------|----------|
| 3000 pcs | 7 inch | 30,000 pcs | 203×203×195 | 120,000 pcs | 438×438×220 | |

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